

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	156	wafer adj pad and inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:04
L2	27	L1 and notch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:04
L3	337122	crystallographic asj structure and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:09
L4	966	crystallographic adj structure and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:09
L5	191	crystallographic adj structure same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:09
L6	150	L5 and (@ad<"20040202" or @rlad<"20040202" or @prad<"20040202" or @ptad<"20040202")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:21
L7	117	L5 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:21
L8	16	L7 and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:22
L9	16	L8 and (compar\$3 or match\$3) and wafer and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:23

L10	41	crystallographic adj structure and wafer and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:39
L11	5	L10 and(compar\$3 or match\$3) and wafer and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:40
L12	4	L11 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:40
L13	110	((("4352948") or ("6161054") or ("5203005") or ("5287472") or ("5292677") or ("5485097") or ("6243308") or ("4435498") or ("4471483") or ("4493055") or ("4519035") or ("4543444") or ("4898835") or ("4999689") or ("5019736") or ("5024972") or ("5252507") or ("5265847") or ("5315130") or ("5362666") or ("5393617") or ("5478363") or ("5491665") or ("5536964") or ("5552243") or ("5619419") or ("5624771") or ("5656392") or ("5657284") or ("5698453") or ("5698342") or ("5716459") or ("5808947") or ("5821160") or ("5851693") or ("5926419") or ("6040912") or ("RE36644") or ("6046078") or ("6140140") or ("6161213") or ("6225167") or ("6330819") or ("4304641") or ("4338480") or ("4353160") or ("4385198") or ("4400221") or ("4400868") or ("").pn.")). PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/10 16:43
L14	106	L13 and(@ad<"20040202" or @rlad<"20040202" or @prad<"20040202" or @ptad<"20040202")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:43
L15	106	L13 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:43
L16	0	L15 and crystallographic adj structure and wafer and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:44

L17	0	L15 and crystallographic adj structure and wafer and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:46
L18	5	L15 and inspect\$3 and (crystallographic adj structure or wafer or ingot or cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:05
L19	4	L18 and(compar\$3 or match\$3) and(solar adj cell or cell crystallographic adj structure or wafer or ingot or cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:06
L20	4	L19 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:07
L21	4742	crystallographic adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:10
L22	4328355	(wafer\$1 or semiconductor or solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:11
L23	98638	L22 and inspect\$3 and(cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:20
L24	153527	L22 and inspect\$3 and(cells or cell or wafer or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:21
L25	4742	crystallographic adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:22
L26	632	L24 and L25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:27
L27	1	L26 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:28

L28	3	inspect\$3 and solar adj cell and matrix and convert\$3 and electricity and solar adj cell and treating and silicon adj wafers and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:32
L29	2	L28 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:33
L30	1	L28 and (compar\$3 or match \$3)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:39
L31	1	L25 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:40
L32	17	L22 and (compar\$3 or match \$3)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:40
L33	3	L32 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:41
L34	1	L32 and crystallographic adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:51
L35	1	L32 and crystallographic adj structure and wafer adj structure and manufactured adj cell and crystallographic adj image and information and sufficient adj establish and correspondence and cell and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:58
L36	1	L32 and crystallographic adj structure and wafer adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:59
L37	1	crystallographic adj structure and wafer adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:59

L38	2	L22 and crystallographic adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:00
L39	0	L38 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:01
L40	1	L25 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:04
L41	607	L25 and inspect\$3 and(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:06
L42	1	L41 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:06
L43	587	L41 and(compar\$3 or match\$3) and (memory or cell or memory adj cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:07
L44	1	L41 and(compar\$3 or match\$3) same(memory or cell or memory adj cell)same wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:08
L45	1	L43 and crystallographic adj structure and wafer adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:09
L46	1	L43 and wafer adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:09
L47	1	L43 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:10
L48	297	L43 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:10

L49	12	L48 and(compar\$3 or match\$3) and wafer and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:11
L50	13	L48 and inspect\$3 and wafer \$1 and(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:12
L51	0	L48 and inspect\$3 adj wafer\$1 same(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:13
L52	0	L48 and inspect\$3 adj wafer\$1 and(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:13
L53	3559	L21 and(wafer\$1 or semiconductor or solar adj cell or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:14
L54	2	L53 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:14
L55	0	L54 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:14
L56	2	L25 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:15
L57	1818	L25 and(wafer\$1 or semiconductor or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:16
L58	237	L25 and(wafer\$1 or semiconductor or memory)and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:16
L59	119	L58 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:16

L60	12	L59 and(compar\$3 or match\$3) and wafer and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:19
L61	38	L25 and inspect\$3 and(compar\$3 or match\$3)and wafer and (solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:28
L62	41	L25 and inspect\$3 and(compar\$3 or match\$3)and wafer and (solar adj cell or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:29
L63	13	L62 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:29
L64	85837	analyz\$3 and(crystalline or crystallographic adj structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:35
L65	18	L64 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:36
L66	1	L65 and(wafer\$1 or semiconductor or memory)and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:36
L67	1	inspect\$3 and photovoltaic adj area and manufactured and crystalline adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:43
L68	0	L67 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:44
L69	0	L65 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:46
L70	0	L64 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:47

L71	31037	L64 and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:47
L72	8	L71 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:47
L73	2	L72 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:48
L74	2106	L71 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit) and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:51
L75	45	L74 and(compar\$3 or match\$3) same(memory or cell or memory adj cell)same wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:52
L76	18	L75 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:52
L77	25	L10 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:17
L78	5	L65 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:48
L79	118795	(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit) and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:49
L80	9	L79 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:49
L81	1	L80 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:49



L82	533	crystallographic adj structure and(wafer or ingot)and section	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:15
L83	161	L82 and analyz\$3 and (crystalline or crystallographic adj structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:16
L84	0	L82 and analyz\$3 and (crystalline or crystallographic adj structure) same ignot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:16
L85	0	L83 and(imaging or ccd or camera or CMOS or IR)and wafer adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:17
L86	120	L83 and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:17
L87	48	L86 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:22
L88	0	L86 and etching and texturisation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:59
L89	7	(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit) and etching and texturisation and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:00
L90	2	L89 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:00
L91	0	L90 and(compar\$3 or match\$3) same(memory or cell or memory adj cell or die)same wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:01
L92	0	L90 and(compar\$3 or match\$3) and(memory or cell or memory adj cell or die)and wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:01

L93	2	L90 and(memory or cell or memory adj cell or die)and wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:01
L94	161	L82 and L83	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:05
L95	0	L94 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)and etching and texturisation and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:06
L96	0	L94 and etching and texturisation and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:06
L97	0	L94 and etching and texturisation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:07
L98	1	L82 and etching and texturisation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:07
L99	20	L82 and solar adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:08
L100	8	L99 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:08
L101	2468	ingot and production adj process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:10
L102	523	L101 and wafer\$3 and production adj process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:11
L103	128	L102 and cell and production adj process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:11

L104	1	L103 and wafer adj position\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:12
L105	75	L103 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:13
L106	0	L105 and cell adj inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:13
L107	75	L105 and(memory or cell or memory adj cell or die)and wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:14
L108	0	L107 and(imaging or ccd or camera or CMOS or IR)and wafer adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:14
L109	12	L107 and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:14
L110	10	L109 and(compar\$3 or match \$3)and(memory or cell or memory adj cell or die)and wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:15
L111	10	L110 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:15
S1	2124	sheela chawan.Xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:40
S2	2338	sheela chawan.Xp.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:46
S3	2	S1 and wafer adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:46

S4	2	S2 and wafer adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:47
S5	22	S1 and wafer adj inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:48
S6	22	S2 and wafer adj inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:48
S7	156	wafer adj pad and inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 16:05

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